NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE60H10 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

General Features

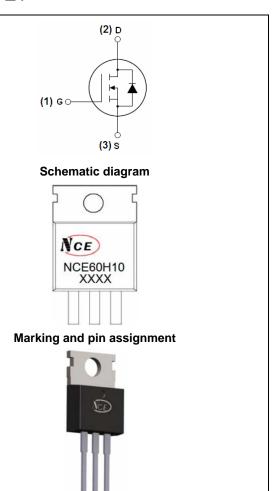
- $V_{DS} = 60V, I_D = 100A$ $R_{DS(ON)} < 5.5 \text{ m}\Omega @ V_{GS} = 10V$ (Typ:4.8m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60H10	NCE60H10	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	100	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	70	Α
Pulsed Drain Current	I _{DM}	320	Α
Maximum Power Dissipation	P _D	170	W
Derating factor		1.13	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	812	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$



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NCE60H10

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	0.88	°C/W	Ī
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Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol Condition		Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	/ _{GS} =0V I _D =250μA 60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V -		-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	On Characteristics (Note 3)					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	2.85	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	4.8	5.5	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	-	50	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -25\/\/ -0\/	-	4900	-	PF
Output Capacitance	Coss	V_{DS} =25V, V_{GS} =0V, F=1.0MHz	-	380	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0WHZ	-	290	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	17	-	nS
Turn-on Rise Time	t _r	VDD=35V,RL=15Ω	-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$	RG=2.5Ω,VGS=10V	-	55	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Q_g	\/ -20\/ L -20A	-	100	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =20A,	-	21	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	30	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	100	Α
Reverse Recovery Time	t _{rr}	Tj=25℃,I _F =100A	-		37	nS
Reverse Recovery Charge	Qrr	di/dt=100A/µs ^(Note3)	-		58	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

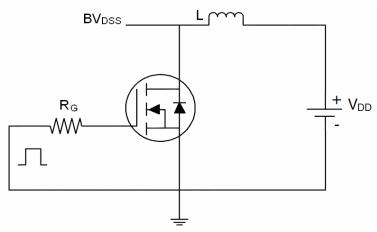
Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature}.$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}\text{C}$,VDD=35V,VG=10V,L=0.5mH,Rg=25 Ω

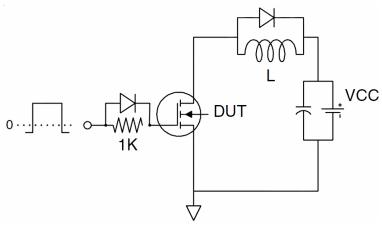
NCE60H10

Test Circuit

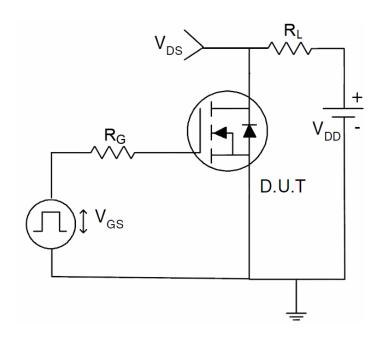
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves

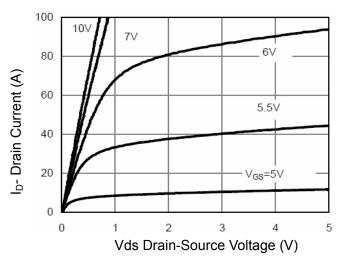


Figure 1 Output Characteristics

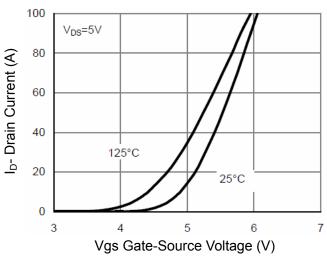


Figure 2 Transfer Characteristics

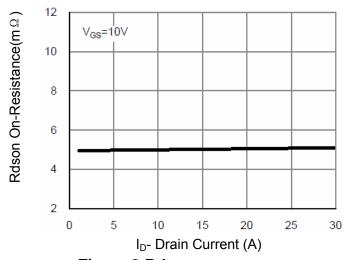


Figure 3 Rdson- Drain Current

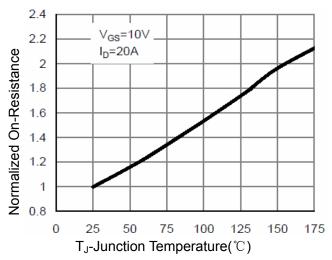


Figure 4 Rdson-Junction Temperature

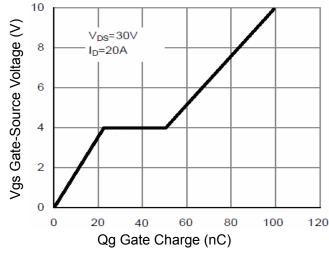


Figure 5 Gate Charge

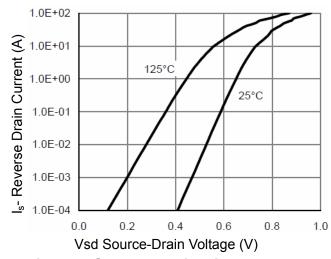
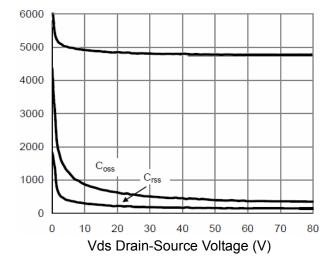


Figure 6 Source- Drain Diode Forward



C Capacitance (pF)



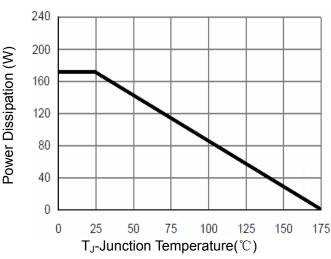
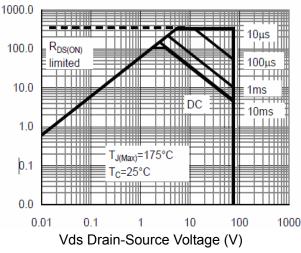


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



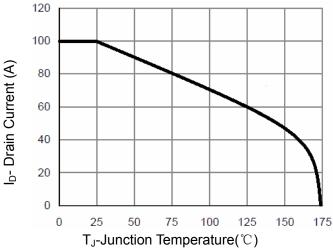


Figure 8 Safe Operation Area

Figure 10 I_D Current De-rating

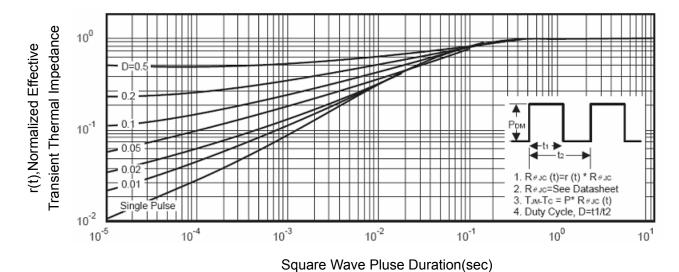
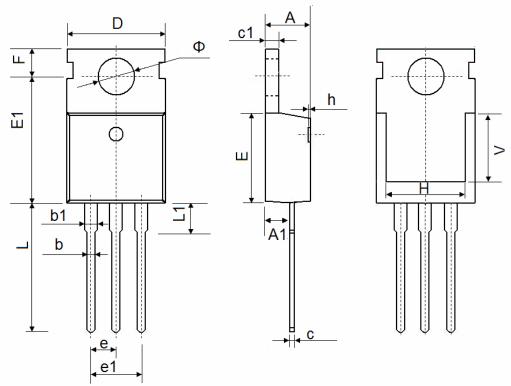


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100	TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500	REF.	0.295	REF.	
Ф	3.400	3.800	0.134	0.150	



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